

ZXSDS2M832

MPPS™ Miniature Package Power Solutions DUAL 60V, 1.65A SCHOTTKY DIODE COMBINATION

SUMMARY

Schottky Diode - $V_R = 60V$; $V_F = 600mV(@1A)$; $I_C=1.65A$

DESCRIPTION

Packaged in the new innovative 3x2 MLP (Micro Leaded Package) outline, this combination dual comprises two 60V 0.9A Schottky barrier diodes. This excellent combination provides users with highly efficient performance in applications including DC-DC converters and charging circuits.

Additionally users gain several other key benefits:

- Performance capability equivalent to much larger packages
- Improved circuit efficiency & power levels
- PCB area and device placement savings
- Lower Package Height (0.9mm nom)
- Reduced component count

FEATURES

- Extremely Low V_F , fast switching Schottky
- $I_F= 1.65A$ Continuous Forward Current
- 3mm x 2mm MLP

APPLICATIONS

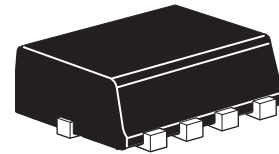
- DC-DC Converters
- DC-DC Modules
- Mosfet gate drive circuits
- Charging circuits
- Mobile Phones
- Motor Control

ORDERING INFORMATION

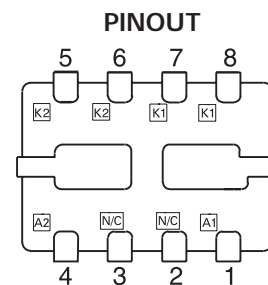
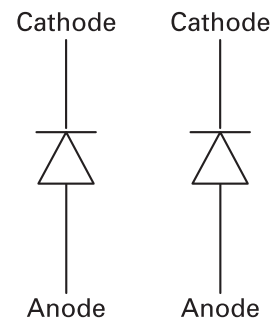
DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXSDS2M832TA	7"	8mm	3000 units
ZXSDS2M832TC	13"	8mm	10000 units

DEVICE MARKING

- DS2



MLP832



Bottom View

ZXSDS2M832

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Reverse Voltage	V_R	60	V
Forward Voltage @ $I_F = 1000\text{mA}$	V_F	600	mV
Forward Current	I_F	1.65	A
Average Forward Current $D=50\%$, $t_{\leq}=300\mu\text{s}$	I_{FAV}	1.24	A
Non Repetitive Forward Current $t_{\leq}=100\mu\text{s}$	I_{FSM}	16.8	A
Non Repetitive Forward Current $t_{\leq}=10\text{ms}$		5.63	A
Power Dissipation at $T_A=25^\circ\text{C}$ (a)(f)	P_D	1.2	W
Linear Derating Factor		12	mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (b)(f)	P_D	2	W
Linear Derating Factor		20	mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (c)(f)	P_D	0.8	W
Linear Derating Factor		8	mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (d)(f)	P_D	0.9	W
Linear Derating Factor		9	mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (d)(g)	P_D	1.36	W
Linear Derating Factor		13.6	mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (e)(g)	P_D	2.4	W
Linear Derating Factor		24	mW/ $^\circ\text{C}$
Storage Temp, Range	T_{stg}	-55 to +150	$^\circ\text{C}$
Operating & Storage Temp, Range	T_j	-55 to +125	$^\circ\text{C}$

THERMAL RESISTANCE

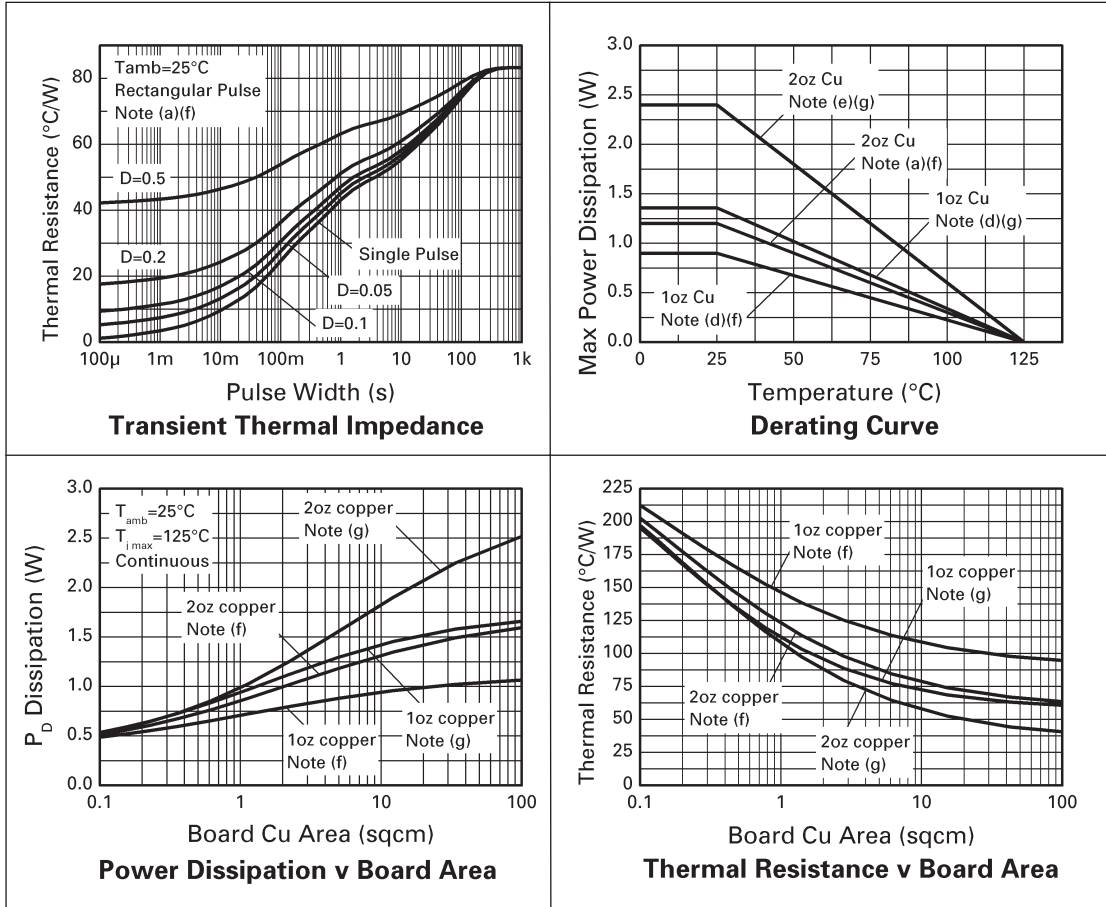
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(f)	$R_{\theta JA}$	83.3	$^\circ\text{C}/\text{W}$
Junction to Ambient (b)(f)	$R_{\theta JA}$	51	$^\circ\text{C}/\text{W}$
Junction to Ambient (c)(f)	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Junction to Ambient (d)(f)	$R_{\theta JA}$	111	$^\circ\text{C}/\text{W}$
Junction to Ambient (d)(g)	$R_{\theta JA}$	73.5	$^\circ\text{C}/\text{W}$
Junction to Ambient (e)(g)	$R_{\theta JA}$	41.7	$^\circ\text{C}/\text{W}$

NOTES

- For a dual device surface mounted on 8 sq. cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the center line into two separate areas with one half connected to each half of the dual device.
- Measured at $t < 5$ secs for a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centerline into two separate areas with one half connected to each half of the dual device.
- For a dual device surface mounted on 8 sq cm single sided 2oz copper FR4 PCB, in still air conditions **with minimal lead connections only**.
- For a dual device surface mounted on 10 sq cm single sided 1oz copper FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centerline into two separate areas with one half connected to each half of the dual device.
- For a dual device surface mounted on 85 sq cm single sided 2oz copper FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centerline into two separate areas with one half connected to each half of the dual device.
- For dual device with one active die.
- For dual device with 2 active die running at equal power.
- Repetitive rating - pulse width limited by max junction temperature. Refer to Transient Thermal Impedance graph.
- The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device as shown in the package dimensions data. The thermal resistance for a dual device mounted on 1.5mm thick FR4 board using minimum copper of 1 oz weight, 1mm wide tracks and one half of the device active is $R_{\theta h} = 250^\circ\text{C}/\text{W}$ giving a power rating of $P_{tot} = 400\text{mW}$.

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TYPICAL CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Reverse Breakdown Voltage	$V_{(BR)R}$	60	80		V	$I_R = 300\mu\text{A}^*$
Forward Voltage	V_F		245	280	mV	$I_F = 50\text{mA}^*$
			275	320	mV	$I_F = 100\text{mA}^*$
			330	390	mV	$I_F = 250\text{mA}^*$
			395	470	mV	$I_F = 500\text{mA}^*$
			455	530	mV	$I_F = 750\text{mA}^*$
			510	600	mV	$I_F = 1000\text{mA}^*$
			620	740	mV	$I_F = 1500\text{mA}^*$
	500	-	mV	$I_F = 1000\text{mA}^*$, $T_A = 100^{\circ}\text{C}$		
Reverse Current	I_R		50	100	μA	$V_R = 45\text{V}$
Diode Capacitance	C_D		17		pF	$f = 1\text{MHz}$, $V_R = 25\text{V}$
Reverse Recovery Time	t_{rr}		12		ns	Switched from $I_F = 500\text{mA}$ to $I_R = 500\text{mA}$ Measured at $I_R = 50\text{mA}$

NOTES

* Measured under pulsed conditions

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TYPICAL CHARACTERISTICS

